

## **NDL SiPm Series EQR15 11-6060D-S**

**1) Test results with 480 nm LED**

**2) Cosmic test**

[www.ndl-sipm.net/PDF/Datasheet-EQR15.pdf](http://www.ndl-sipm.net/PDF/Datasheet-EQR15.pdf)

**NDL (Novel Device Laboratory, Beijing) <http://www.ndl-sipm.net/indexeng.html>**

# NDL SiPM Series EQR15

## 11-6060D-S

[www.ndl-sipm.net/PDF/Datasheet-EQR15.pdf](http://www.ndl-sipm.net/PDF/Datasheet-EQR15.pdf)

- For a conventional SiPM, the quenching resistors are usually fabricated on the surface, and used to connect all APD cells to trace metal lines. In contrast, NDL SiPM **employs intrinsic epitaxial layer as the quenching resistors (EQR)**, and uses a continuous silicon cap layer as an anode to connect all the APD cells. **As a result, the device has more compact structure and simpler fabrication technology, allows larger micro cell density (larger dynamic range) while retaining high photon detection efficiency (PDE).**
- Для обычного SiPM гасящие резисторы обычно изготавливаются на поверхности и используются для соединения всех ячеек APD с металлическими линиями. Напротив, NDL SiPM использует собственный эпитаксиальный слой в качестве гасящих резисторов (EQR) и использует непрерывный слой кремния в качестве анода для соединения всех ячеек APD. **В результате устройство имеет более компактную структуру и более простую технологию изготовления, позволяет увеличить плотность микроячеек (большой динамический диапазон) при сохранении высокой эффективности детектирования фотонов (PDE).**
- NDL (Novel Device Laboratory, Beijing) <http://www.ndl-sipm.net/indexeng.html>



# EQR15 Series SiPMs

Specifications subject to change without notice



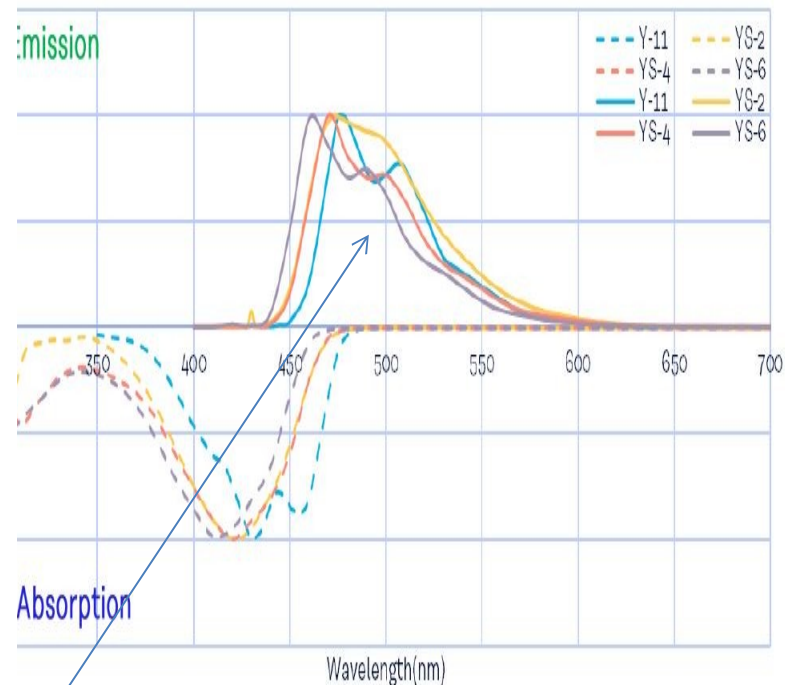
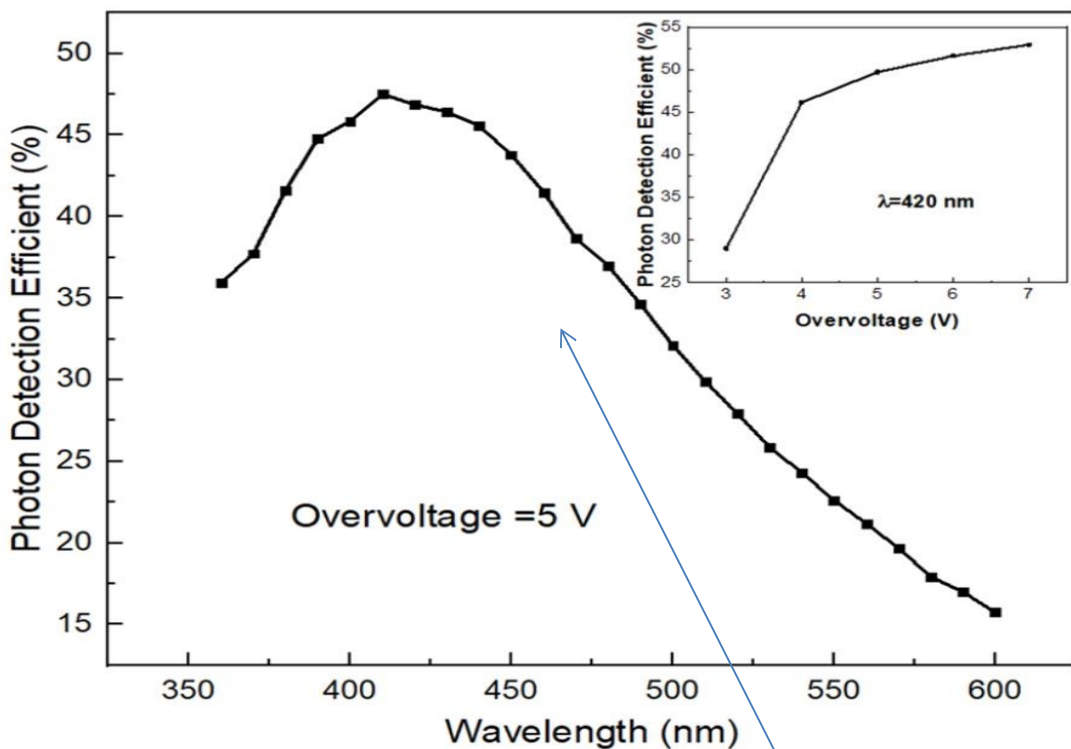
Type	EQR15 11-1010D-S	EQR15 11-3030D-S	EQR15 11-6060D-S	EQR15 22-1313D-S
Effective Pitch	15 $\mu\text{m}$			
Element Number	1 $\times$ 1			2 $\times$ 2
Active Area	1.0 $\times$ 1.0 $\text{mm}^2$	3.0 $\times$ 3.0 $\text{mm}^2$	6.0 $\times$ 6.0 $\text{mm}^2$	1.3 $\times$ 1.3 $\text{mm}^2$
Micro-cell Number	4444	40000	160000	7396
Typical Breakdown Voltage ( $V_B$ )	30 V			
Temperature Coefficient for $V_B$	28 mV/ $^{\circ}\text{C}$			
Recommended Operation Voltage	$V_B + 8 \text{ V}$			
Peak PDE @ 420nm	45 %			
Gain	$4.0 \times 10^5$			
Dark Count Rate (DCR)	250 kHz / $\text{mm}^2$			
Terminal Capacitance	5.6 pF / $\text{mm}^2$			

Above parameters is measured at their recommended operation voltage and 20  $^{\circ}\text{C}$ , and it can operate at 77 K.



# EQR15 Series SiPMs

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Photon Detection Efficient (PDE) correspond to WLS Emission spectra of Y11. PDE close to flat maximum about 45% at 6-7 Overvoltage.

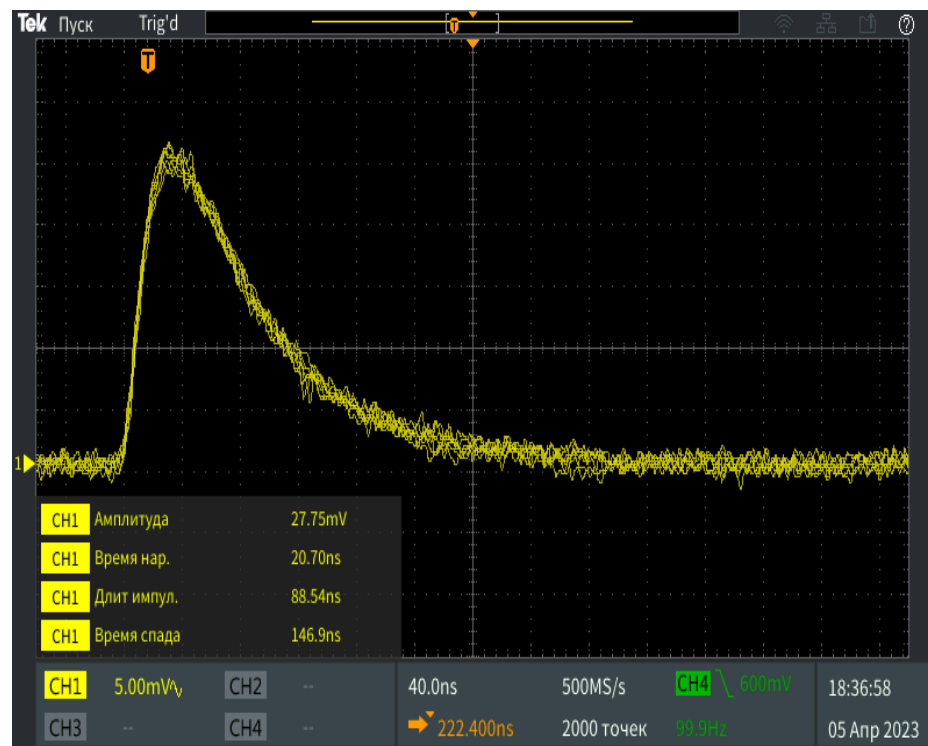
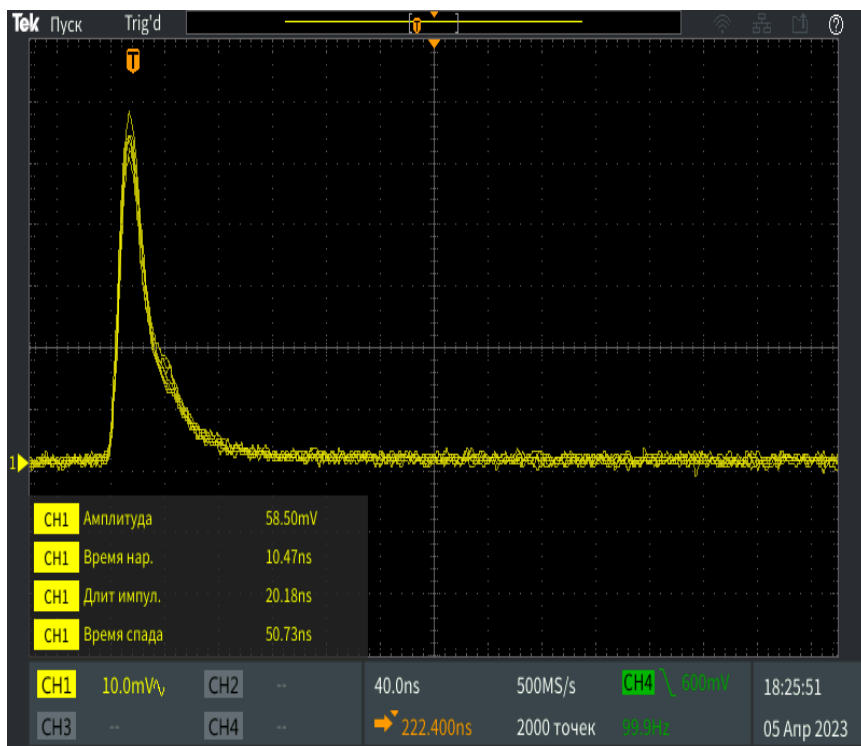


# EQR15 Series SiPMs

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Pulse shape of SiPM with 15  $\mu$  pitch and 6x6 mm<sup>2</sup> size – frm 10 ns LED



EQR11-15-6060-S

Front – 10 ns

Length – 20 ns

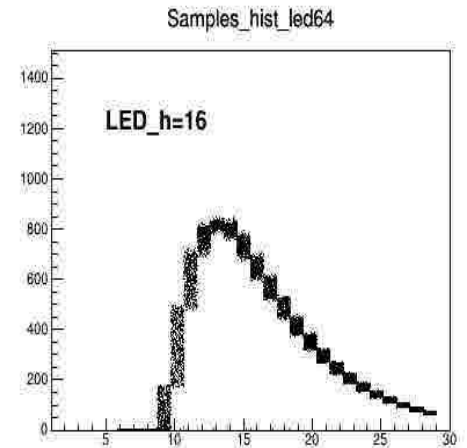
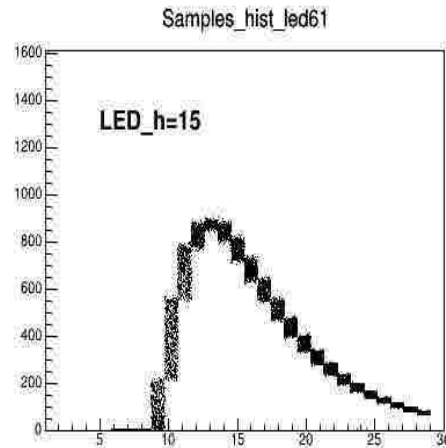
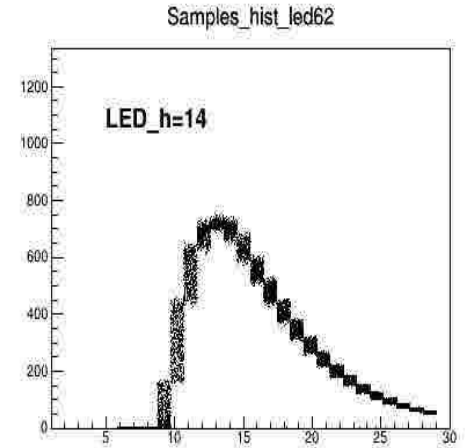
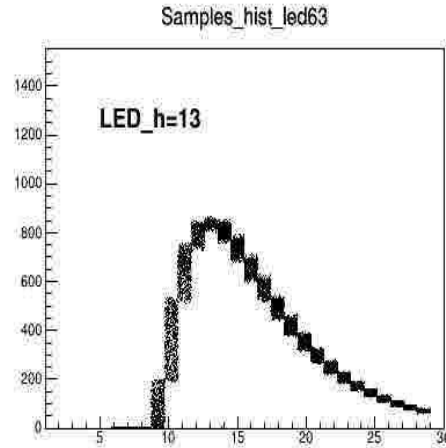
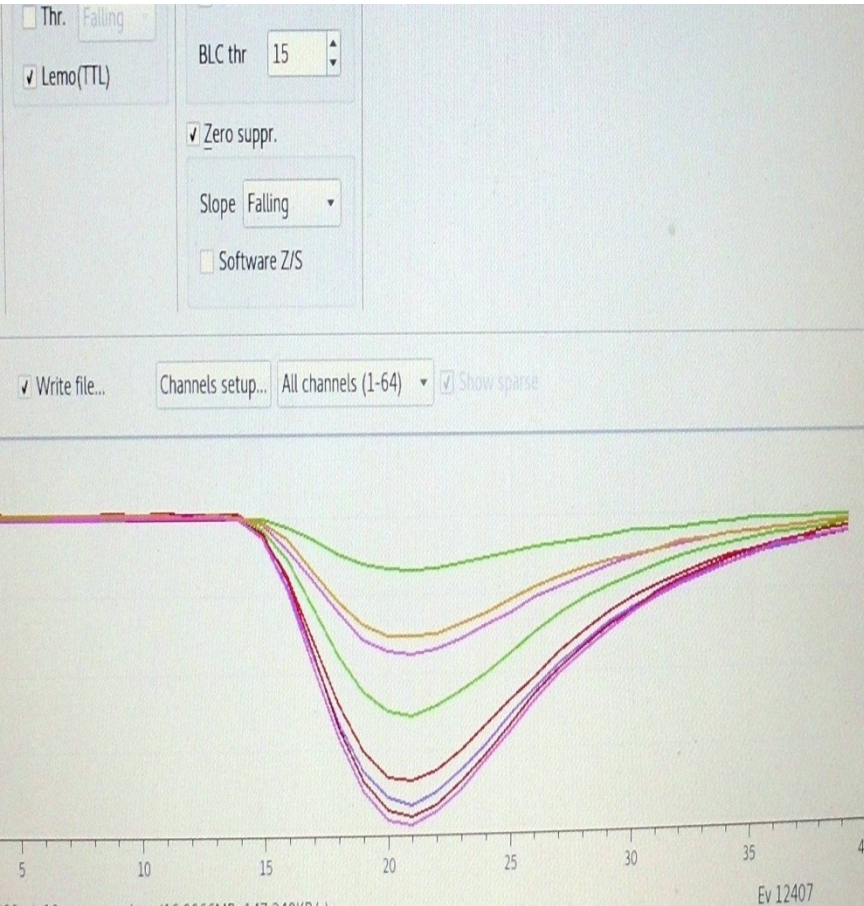
HAMAMATSU S14160-50

Front – 21 ns

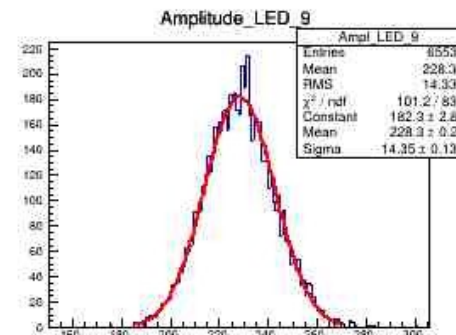
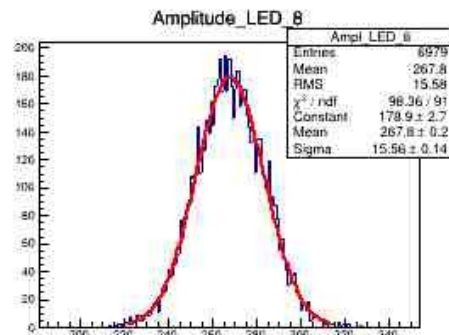
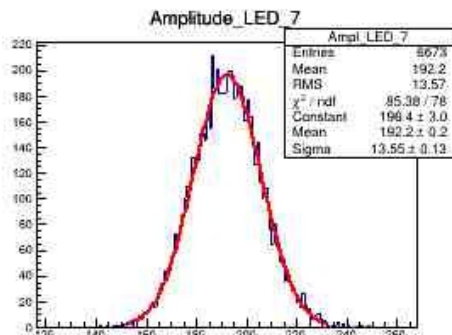
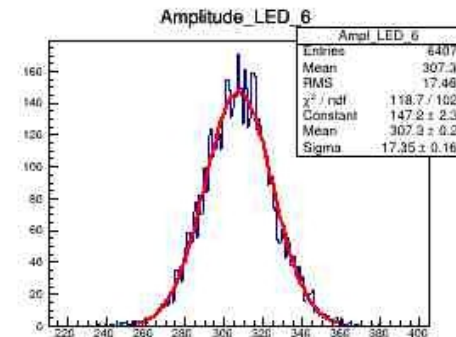
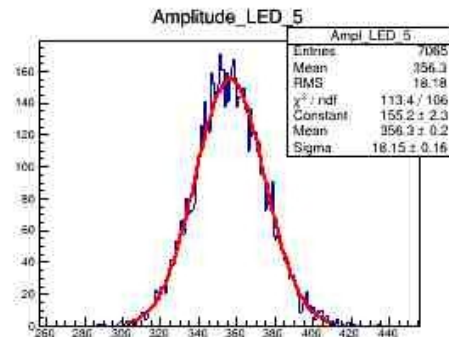
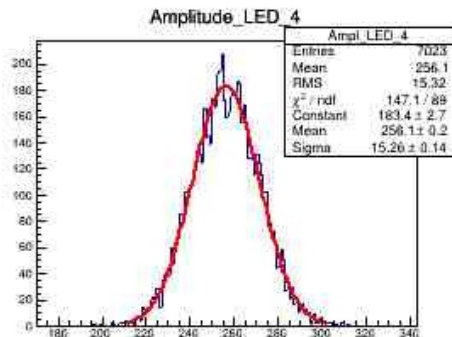
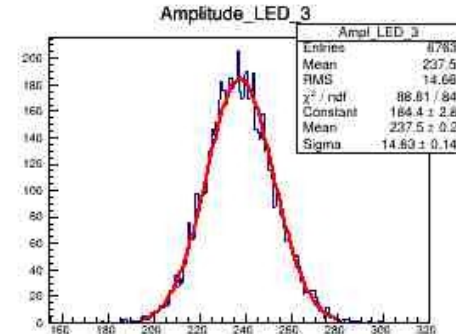
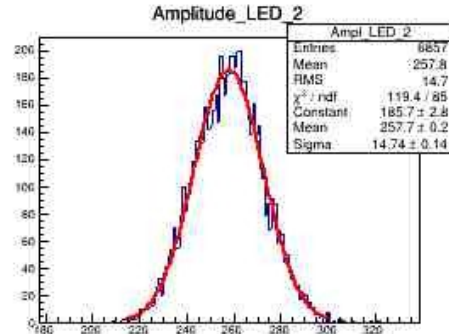
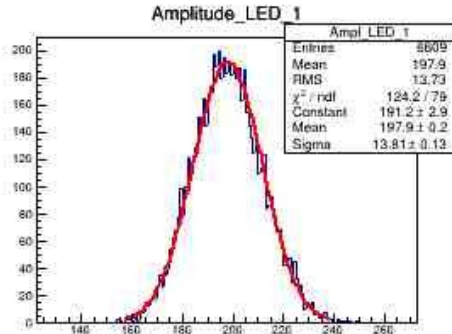
Length – 89 ns



# Wave form and digitizing

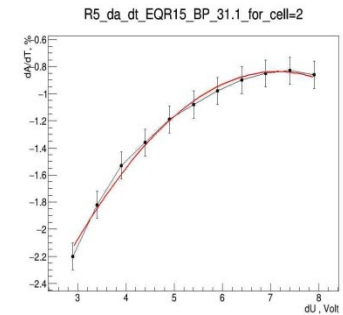
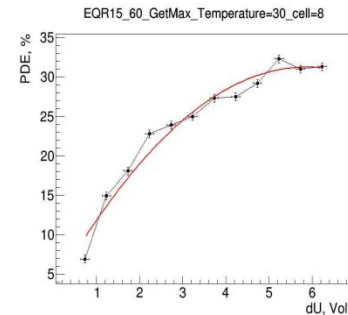
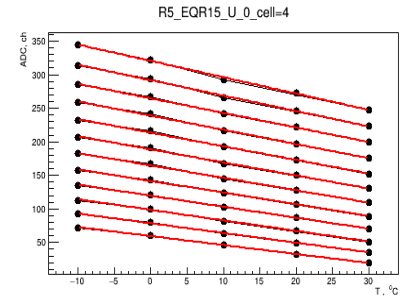
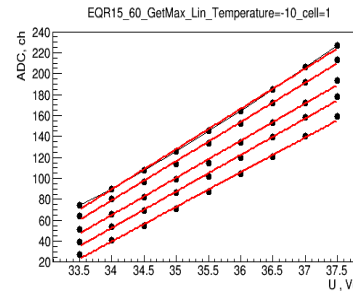
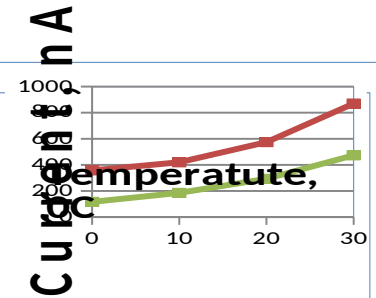
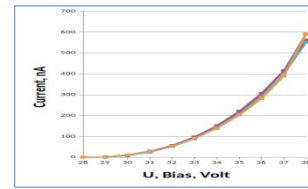


LED amplitudes to caclucte Number Pixel Fired = {Amean/sigma}\*\*2



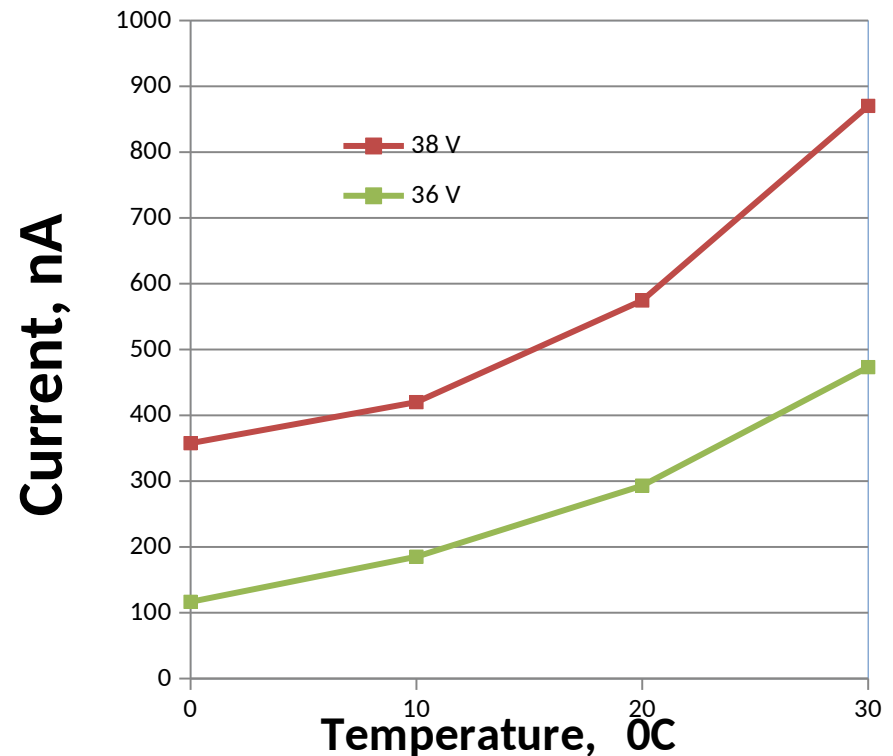
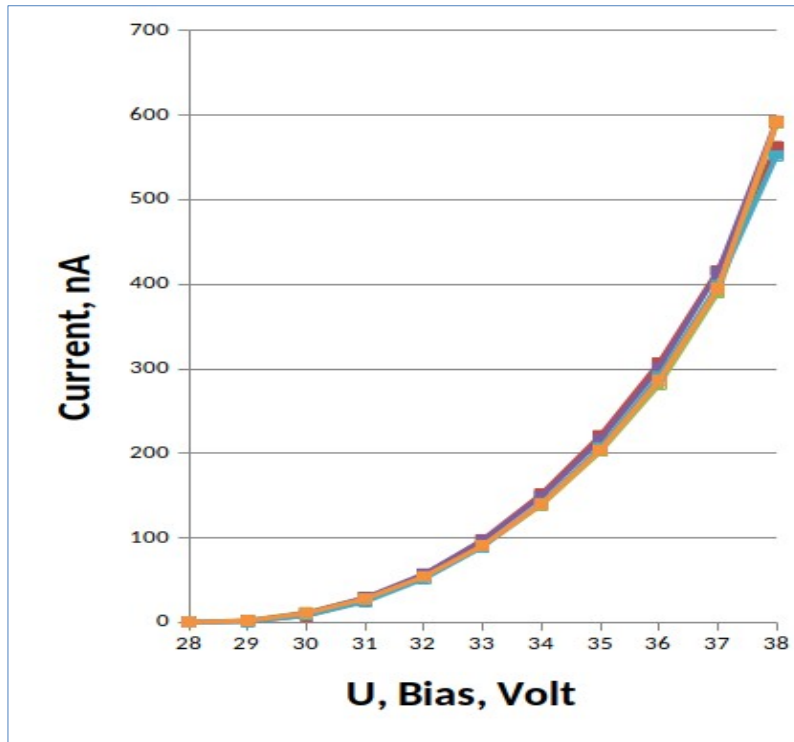
# SiPm test Results

- Dark Current measurements
- Gain vs Overvoltage:  $dA/dU$
- Gain vs Temperature:  $dA/dt$
- PDE vs Overvoltage
- Operation Volt. how to select it ?
- Temperature stability studies



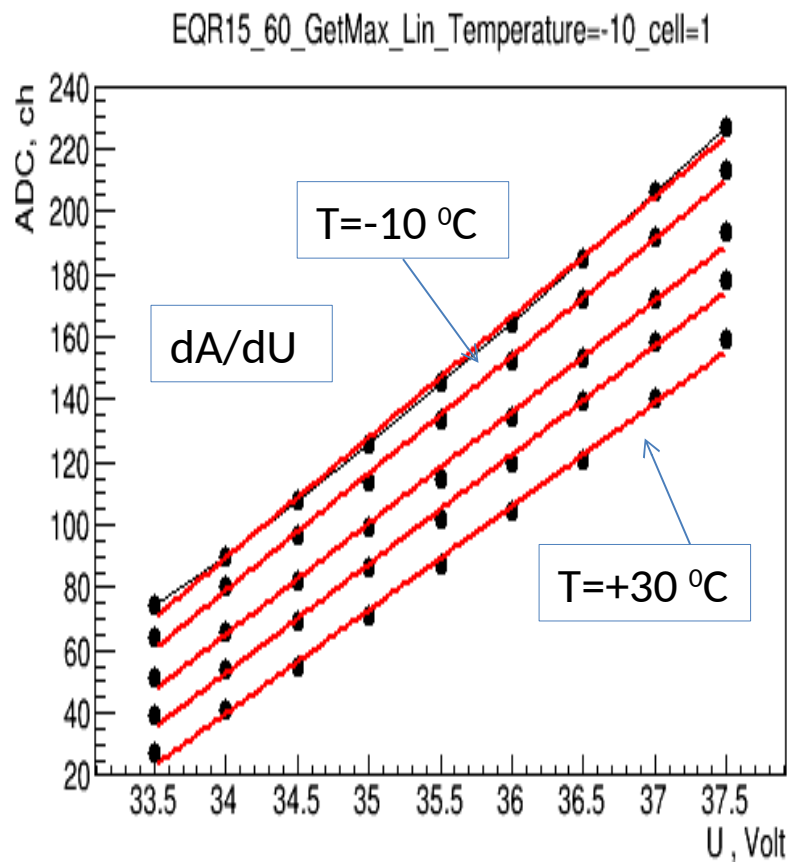


# EQR15-60 Dark Current vs Bias voltage and its temperature dependences around operate Voltage

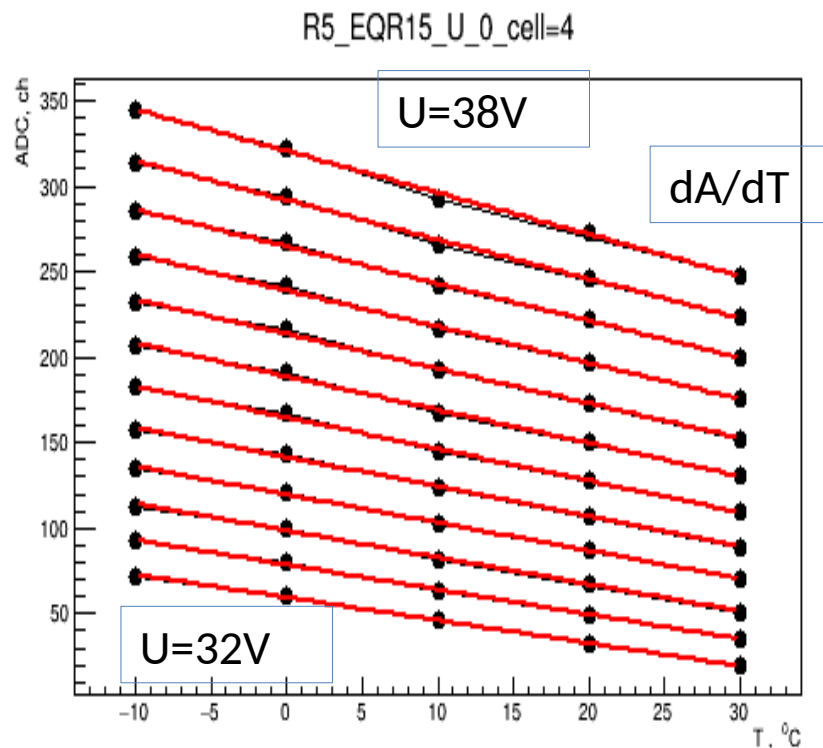


Dark Current vs Operation Bias (36-37 V) at room temperature (20 °C) is equal to 300-400 nA. Its are corresponded to the factory data and is similar HAMAMATSU too.

Gain vs Overvoltage allow obtain:  
slope= $dA/dU$  vs  $U$



Gain vs Temperature allow obtain:  
slope= $dA/dT$  vs  $T$

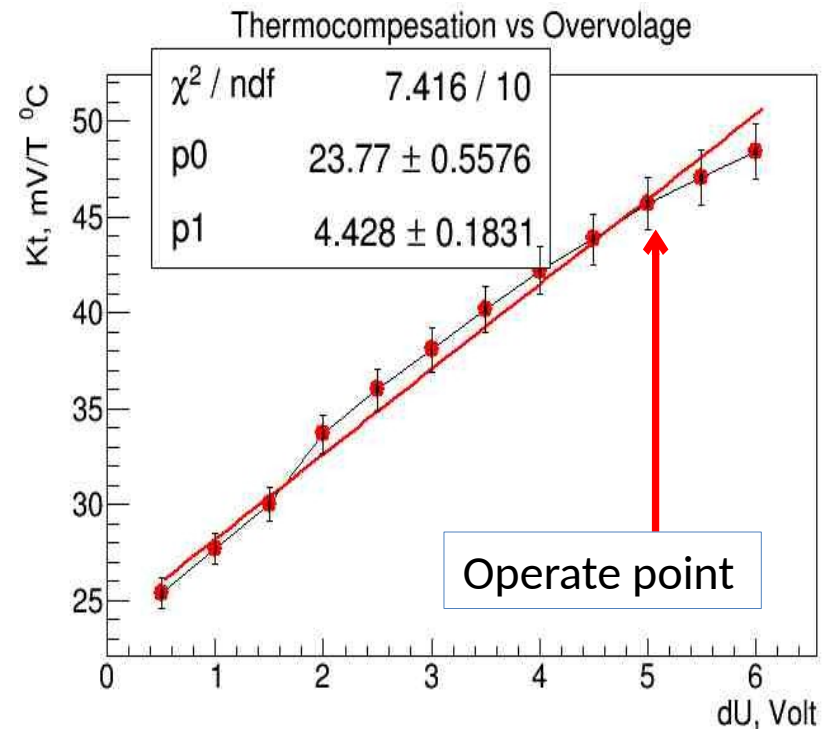
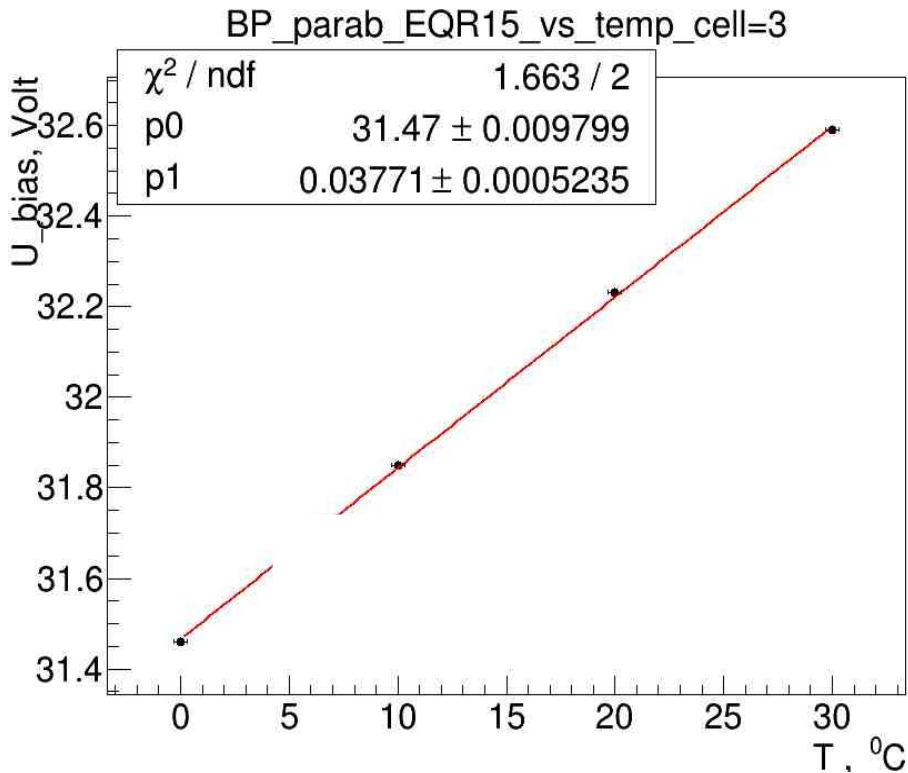


$$K_t = dU/dT = dA/dT / dA/dU$$

The thermal stabilization coefficient ( $K_t$ ) was defined as the ratio of the slope  $dA/dT$  to the slope  $dA/dU$  depending on the applied bias.

Break Point (Bp) was defined as extrapolation point of  $dA/dU$  to zero. Take assumption his linear behavior from Temperature we find that  $Bp=32$  V at  $20$  °C.

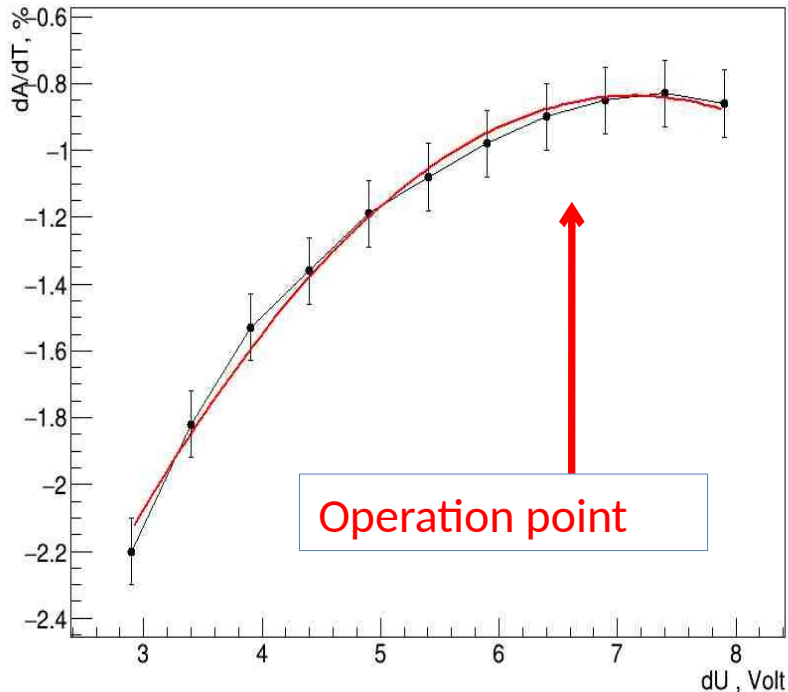
$K_t=dU/dT=dA/dt/dA/dU$  fom previous slides we find that dependence from Overvoltage has linear behavior and equal to  $\sim 50$  mv/°C at Operation point 5.5 V.



# Temperature sensitivity vs dU

## dA/dT vs dU

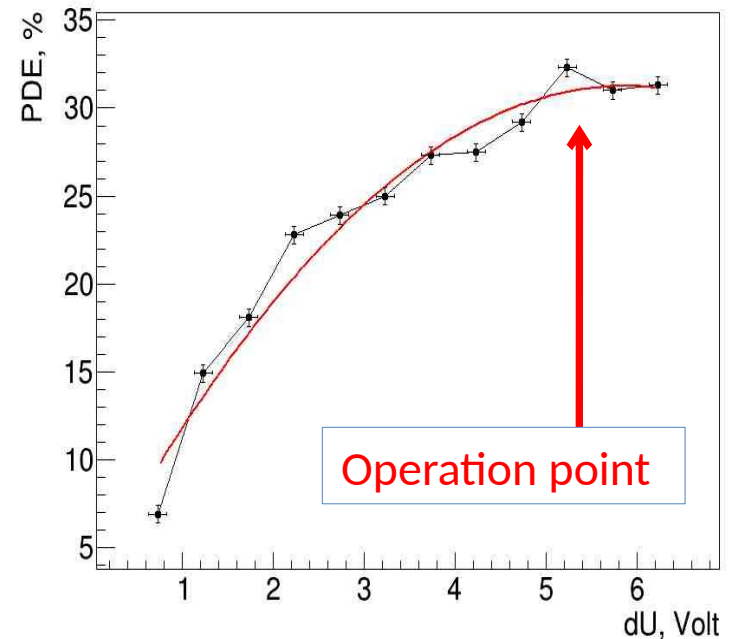
R5\_da\_dt\_EQR15\_BP\_31.1\_for\_cell=2



# Photon Detection Efficient vs dU

## PDE vs dU

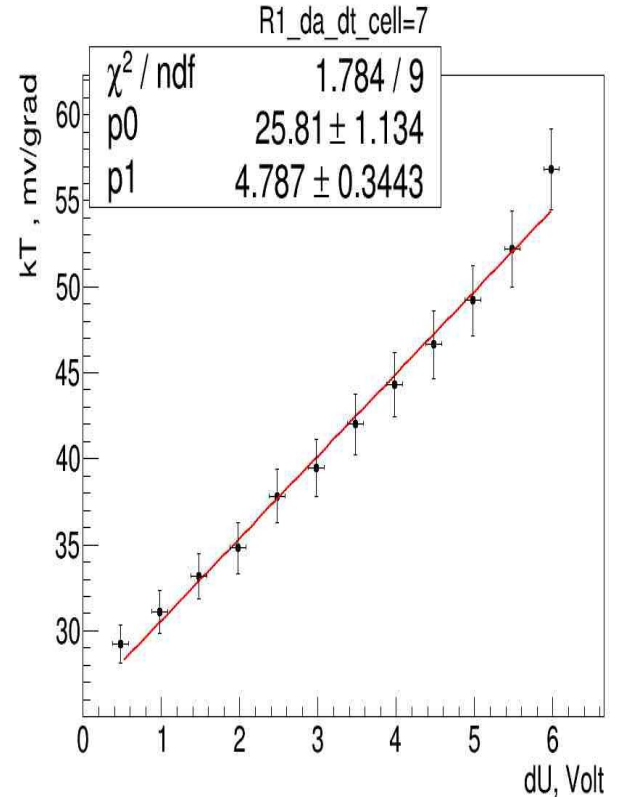
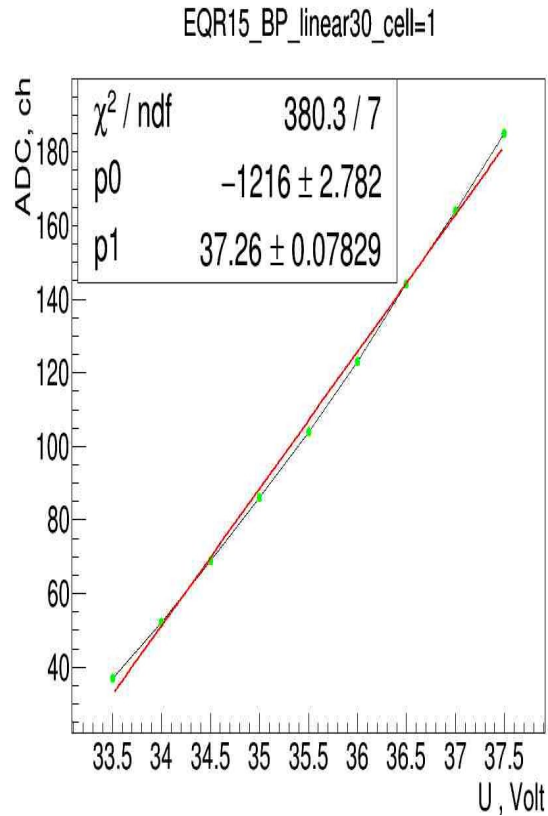
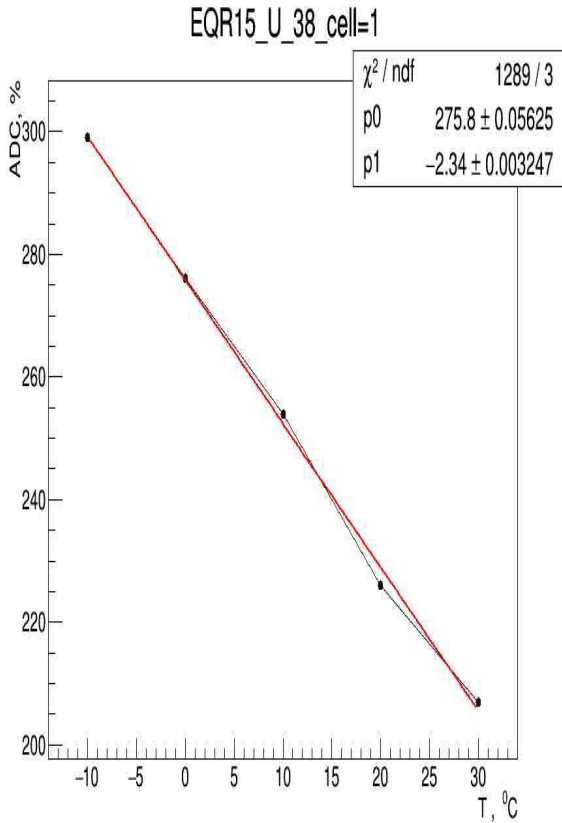
EQR15\_60\_GetMax\_Temperature=30\_cell=8



Operation point was found at  $dU=6.5$  V take in account that:

1.  $dA/dT$  and PDE – has Plato in  $dU$ .
2.  $dA/dT$  has minimal value  $\sim 1\%/^{\circ}\text{C}$ , PDE close to maximal value  $\sim 32\%$ .

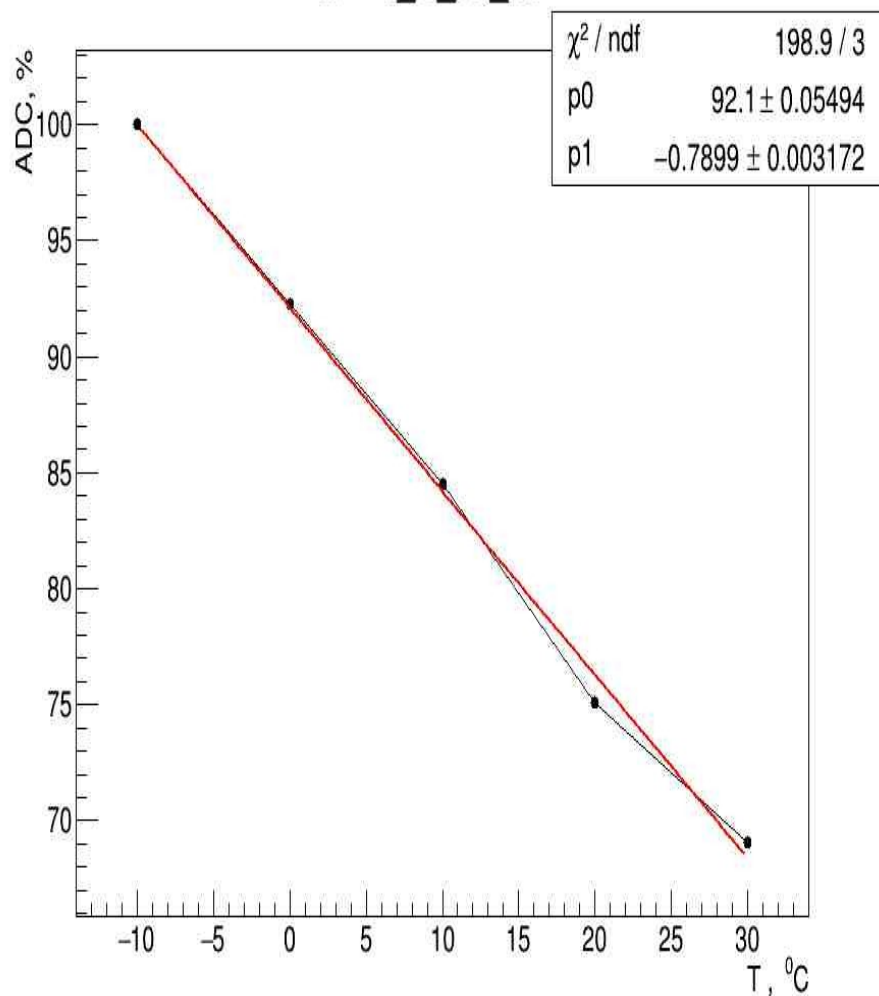
$$Kt = dA/dT / dA/dU$$



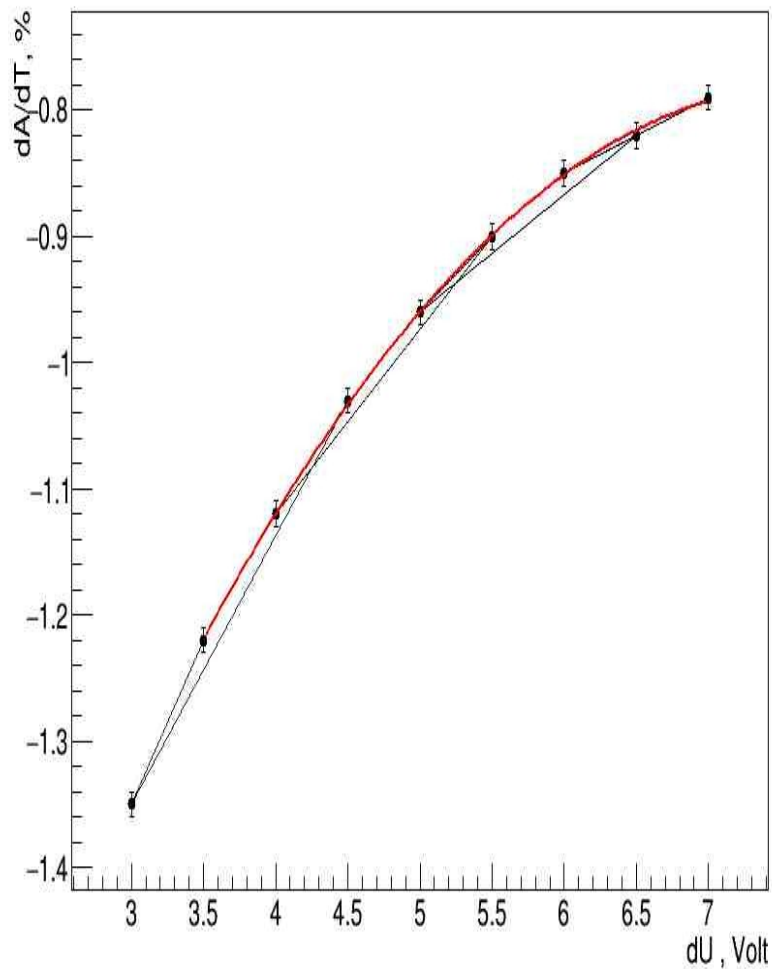


# dA/dT % vs Overvoltage

EQR15\_U\_38\_cell=7



EQR15\_BP\_31\_for\_cell=7



# Test results with cosmic particles

1. 4 Module 3x3 cell with sizes 40x40 mm – MPD option 2012
2. Cosmic beam
3. Event selection = only One cell – one hit events
4. LED monitoring – 1 Hz permanently
5.  $K_t = 20, 30, 40, 50$  mv/Grad for different modules
6. Mip resolution = 9.7 %
7. Long time stability at  $K_t=50$  mv/Grad

# Test results with cosmic particles



Cosmic Rays

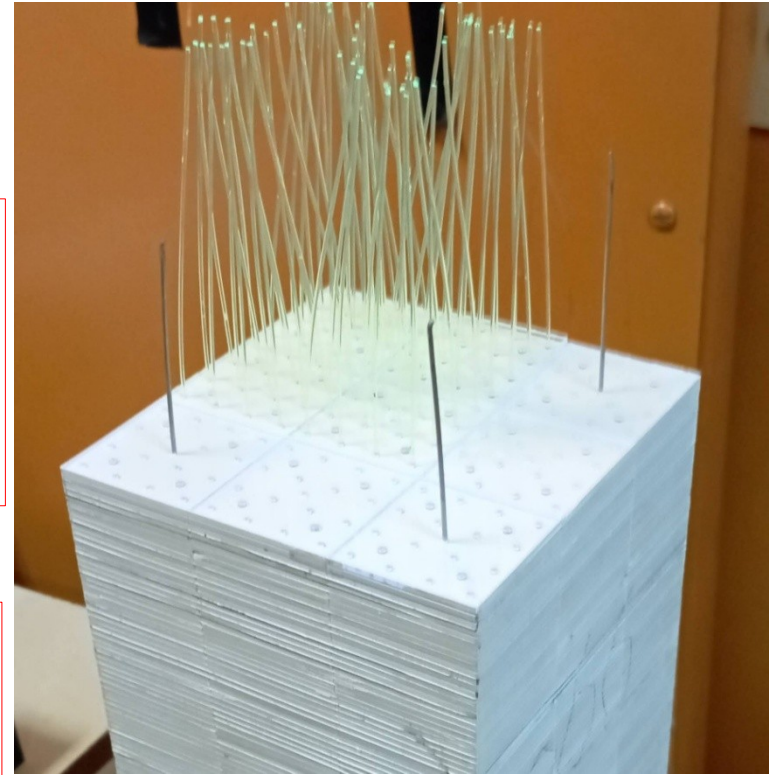
**Setup of 4 modules.**  
Each module consist from 9 cells of 4x4 cm<sup>2</sup>. Totally tested 36 cells.

## Sampling:

- 1.5 mm Scintillator
- 0.3 mm Lead
- 200 layers

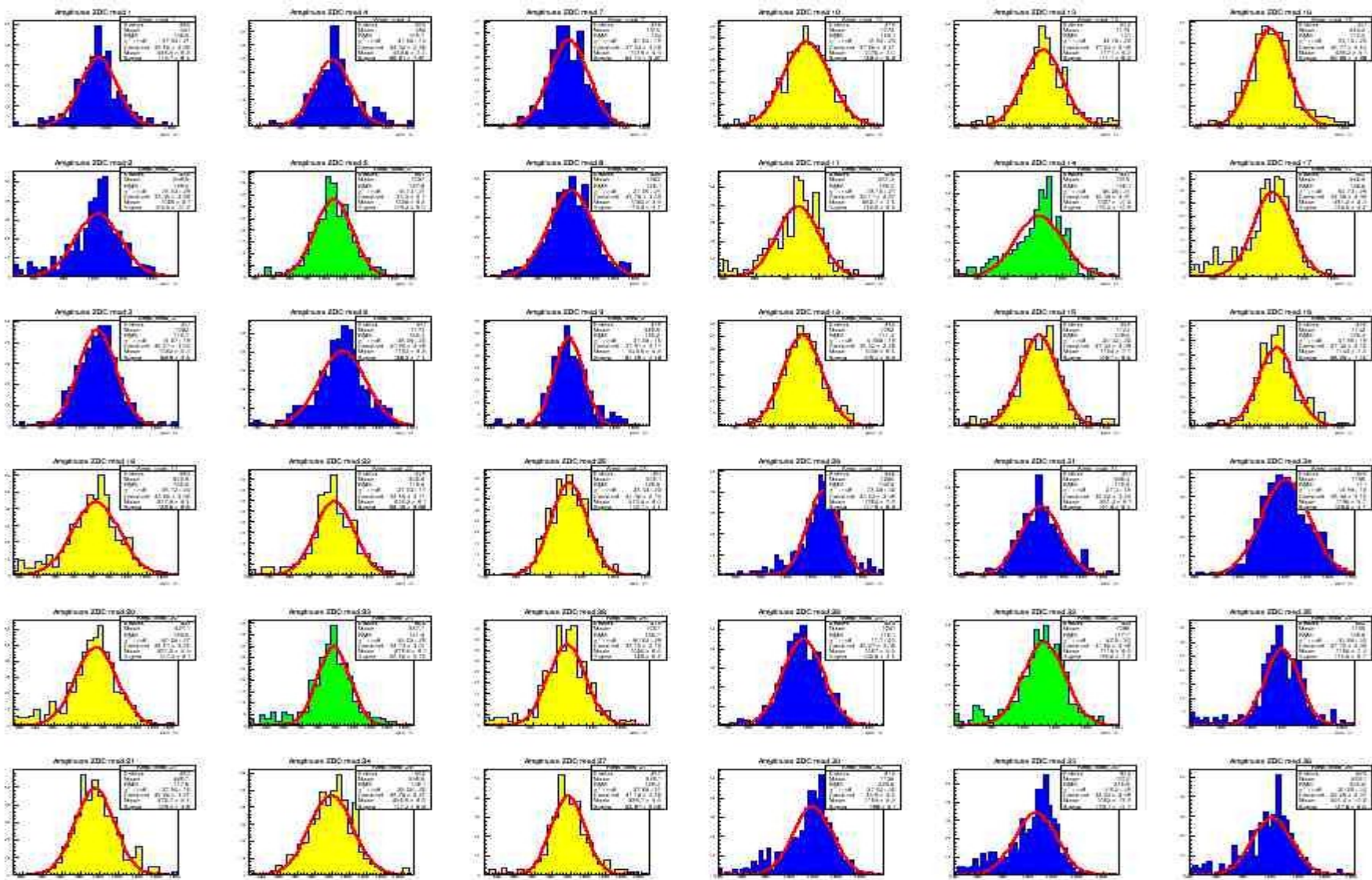
Scintillator composition:

- Polyesterene
- 1.5% Paterphenyle
- 0.04% POPOP



**Single Ecal module shown in assembling stage.**

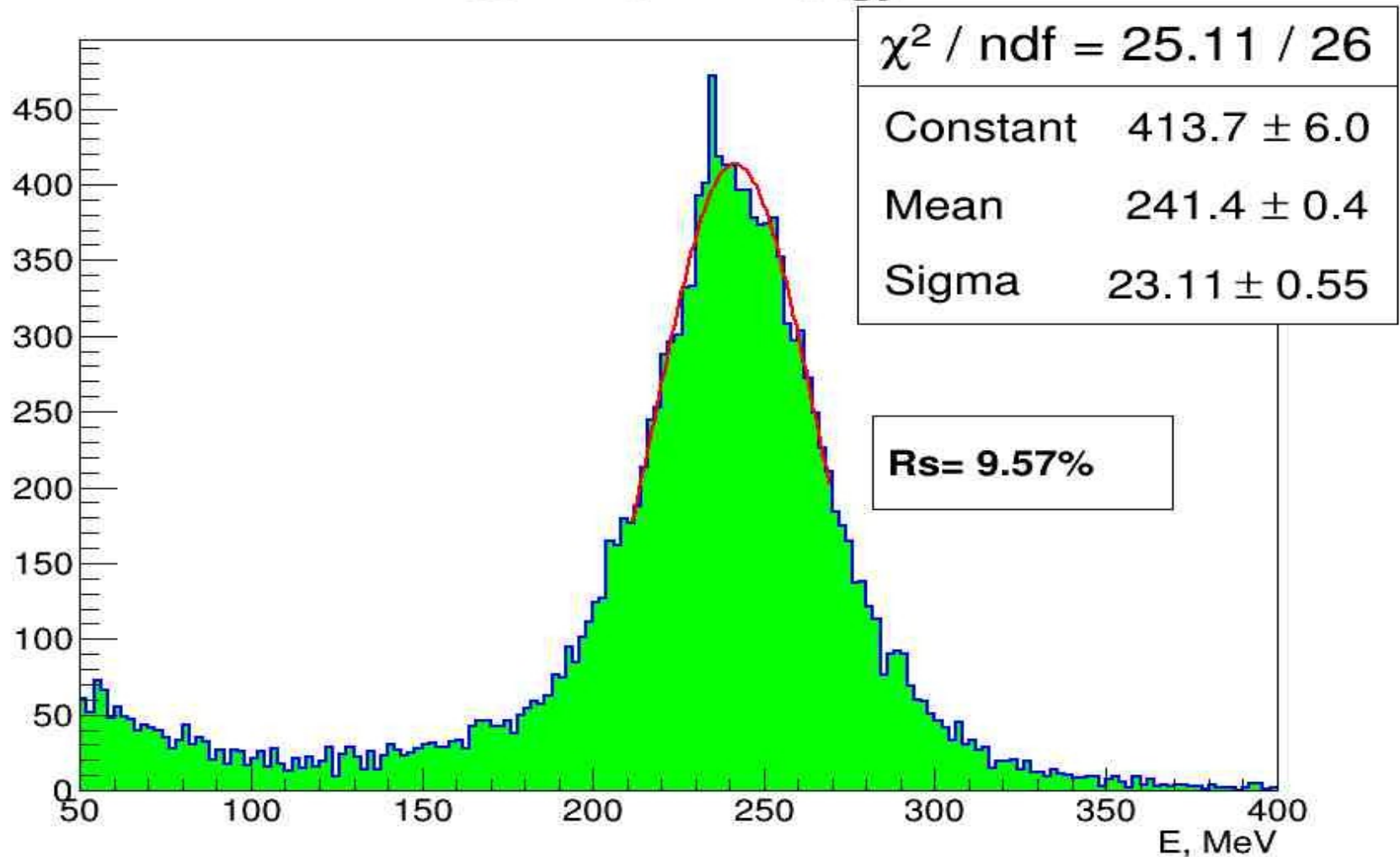
It is visible 9 cells as 3x3 matrix with WLS fibers (16 per cell). Y11(200) diameter 1.0 mm was used.



MIP spectra from 36 Cells. Top view shown on picture Above. One hit/event  
 - applied selection criteria during analysis.  
 Calibration coefficients were found and normalized to 240 MeV.



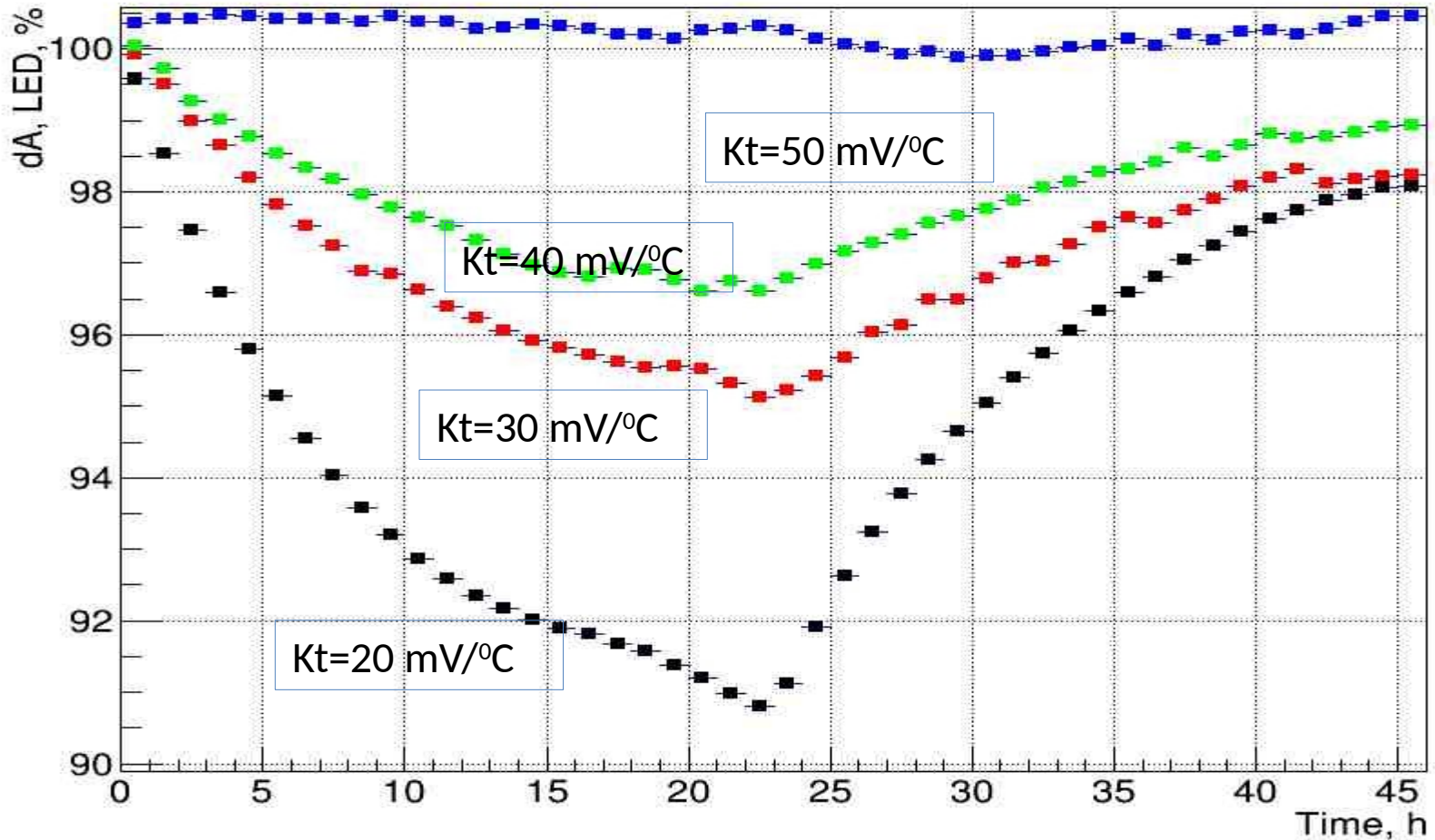
# Sum ECAL Energy



MIP spectra from 36 Cells as Total Sum take in account the Calibration coefficients normalized to 240 MeV. These Energy resolution corresponded to MC

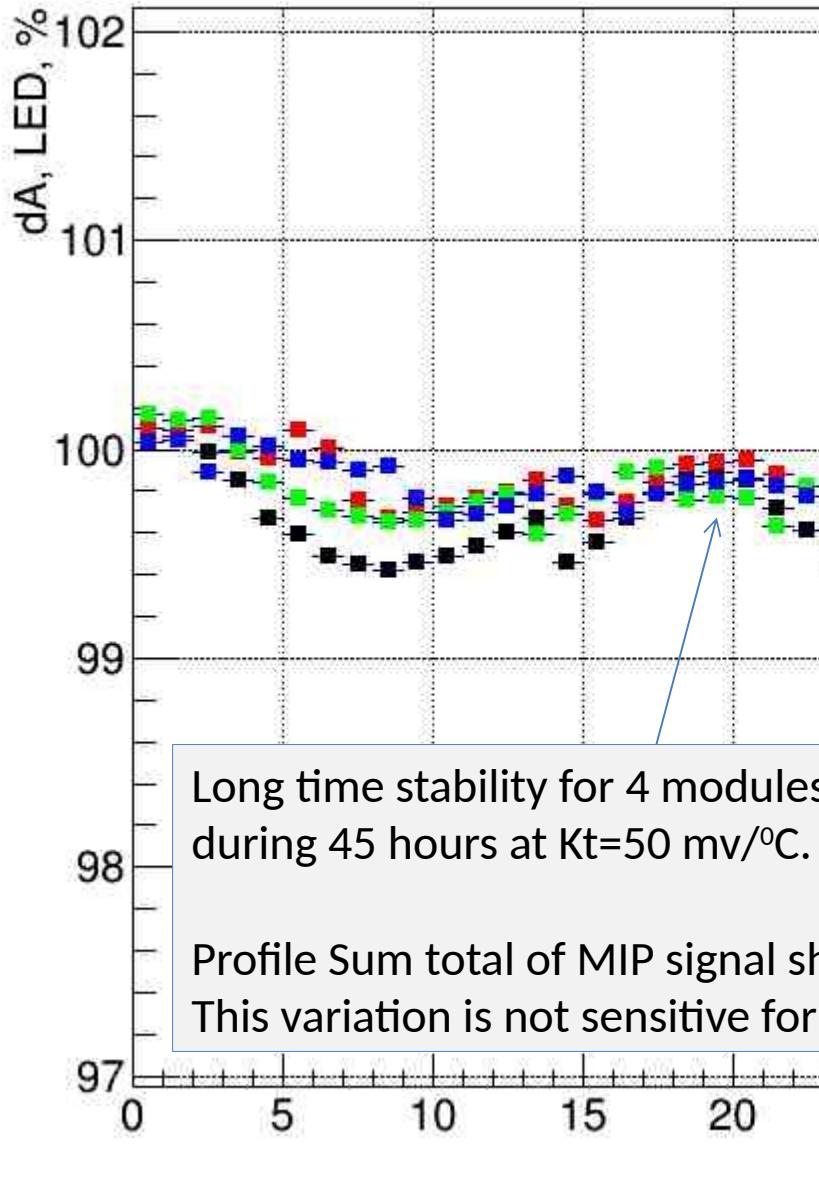


## Profile\_LED\_1\_vs\_Evt\_with\_Temp\_compensation

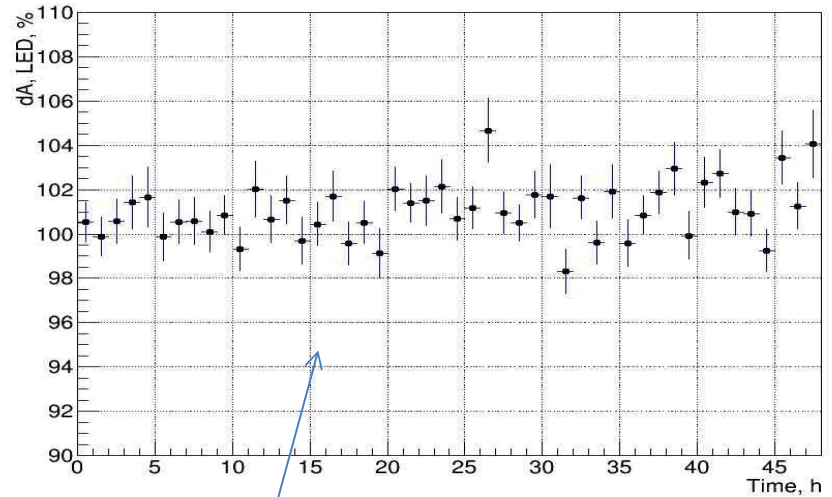


Test of long time Stability was done with different Kt for individual module. The temperature variation from 20 to 30 °C per day was applied.

### Profile\_LED\_1\_vs\_Evt



### Profile\_Sumtot\_vs\_Evt

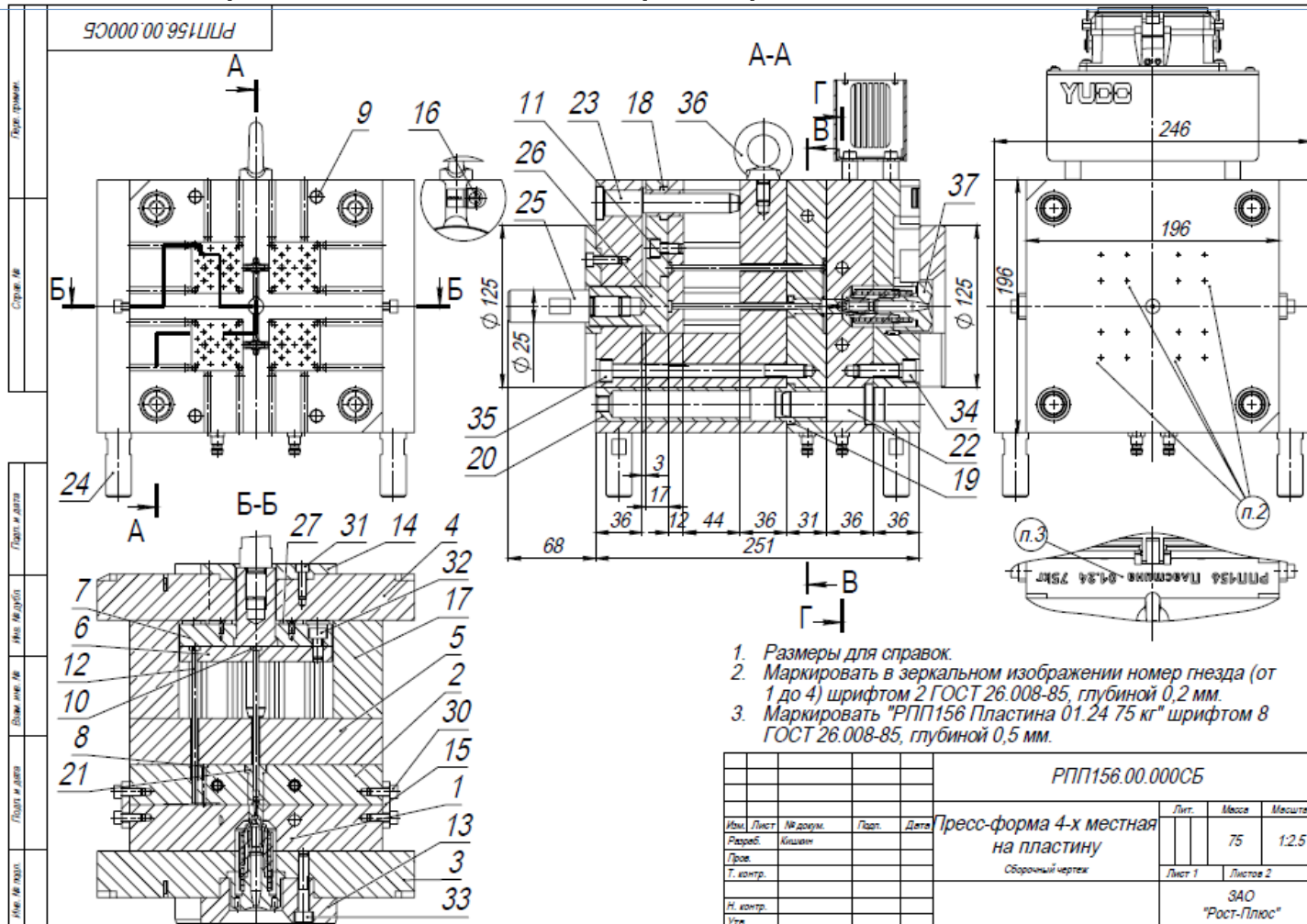


Long time stability for 4 modules shown  $\pm 0.5\%$  LED signal variation during 45 hours at  $Kt=50 \text{ mv}/^{\circ}\text{C}$ .

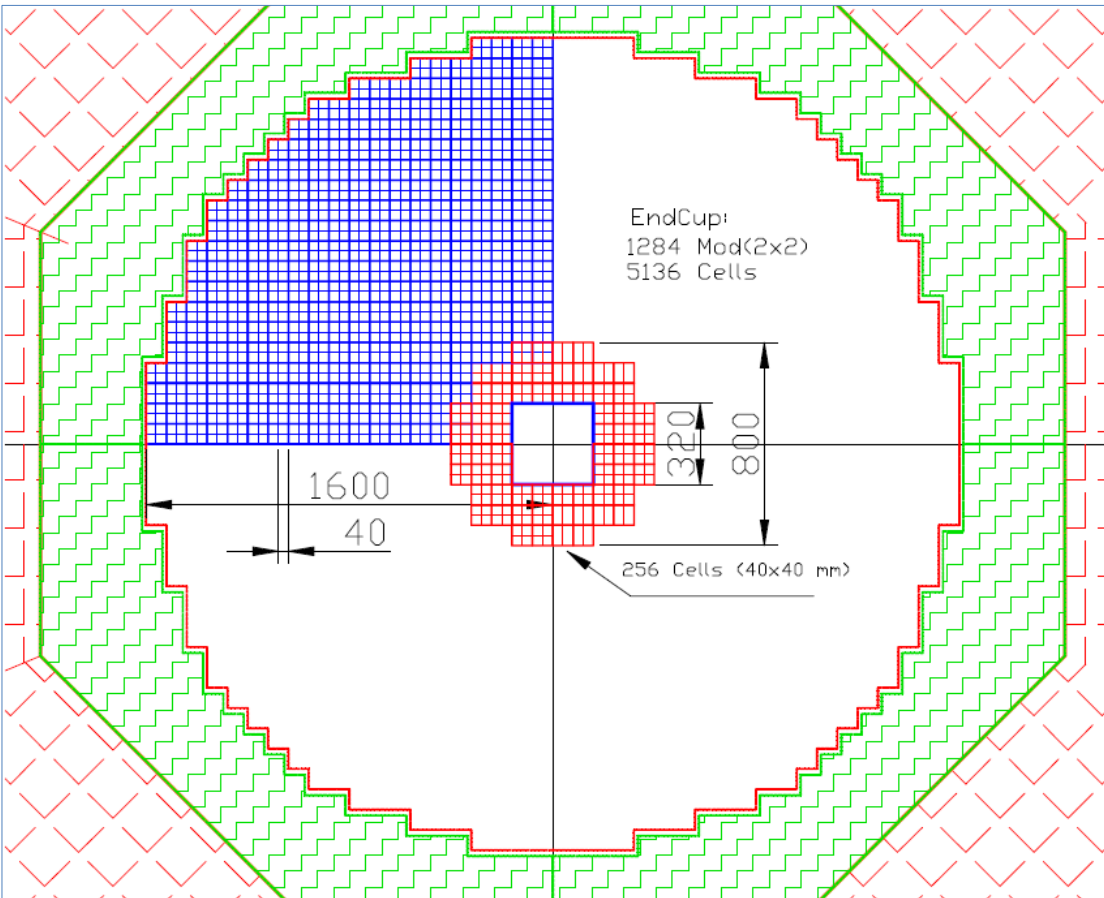
Profile Sum total of MIP signal shown  $\sim 1\%$  variation during 45 hours. This variation is not sensitive for MIP spectra with 9% resolution.

# Matrix form for new scintillator production (40x40x1.5 mm<sup>3</sup>) should be ready in end of 2023

Matrix firm is special setup for molding by pressure technology  
 It allow produce scintillator from granulated polystyrene with doppands  
 4 set form produce 4 scintillator plate per 1 minute



**Plan for 2024:  
End Cup for SPD with new scintillator to be produced in  
February-March of 2024  
256 cells of 40x40 mm<sup>2</sup> = 64 modules of 4 cells=2x2**



This Figure shows in red 64 modules, consisting of 4 cells each. The weight of this assembly is 597 kg. This will require 130 kg of polystyrene, 465 kg of lead, as well as additives: 1.95 kg of P-terphenyl and 65 g. POPOP, and 2000 meters WLS fiber type Y-11. **It is 1/20 part of End Cup and taken time of 36 Days to prepared 51200 Stint. plates.** To read this setup, we need four ADC64 - 64-channel amplitude encoders, as well as 16 boards of 16-channel amplifiers and bias voltage regulators.